

特開平3-173471(2)

線経路111および112を得ることにより、制限を満たす配線長dの配線経路211を得ていた。

(発明が解決しようとする課題)

上述した従来のマスクスライス方式LSIの配線構造では、高速動作を必要とするLSIの遅延時間等の制約を満足するために設定された配線長に制限がある配線ネットの配線において配線処理後にその制限が満たされなかった場合に、制限を満たすようにするために他の配線を移動させて配線の修正を行う必要があったので、配線の修正に多大な工数を要するという欠点がある。

また、配線の修正を行っても配線長の制限を満たすことができなかった場合には、ブロックの配線修正等を行って配線処理をやり直す必要があり、さらに処理時間が増大するという欠点がある。

本発明の目的は、上述の点に鑑み、第1の配線層および第2の配線層に定義された垂直方向および水平方向の配線格子の各格子点の対角を結ぶ斜めの配線格子が定義された第3層の配線層を利用

して、他の配線を移動したりブロックの配置位置を変更したりすることなしに、比較的容易に配線長の調整を行うことができるマスクスライス方式LSIの配線構造を提供することにある。

(課題を解決するための手段)

本発明のマスクスライス方式LSIの配線構造は、垂直方向および水平方向の配線格子が定義された第1の配線層および第2の配線層と、これら第1の配線層および第2の配線層に定義された垂直方向および水平方向の配線格子の各格子点の対角を結ぶ斜めの配線格子が定義された第3の配線層とを有する。

(作用)

本発明のマスクスライス方式LSIの配線構造では、第1の配線層および第2の配線層に垂直方向および水平方向の配線格子が定義され、第3の配線層に第1の配線層および第2の配線層に定義された垂直方向および水平方向の配線格子の各格子点の対角を結ぶ斜めの配線格子が定義される。

(実施例)

次に、本発明について図面を参照して詳細に説明する。

第1図は、本発明の一実施例に係るマスクスライス方式LSIの配線構造を示す図である。本実施例のマスクスライス方式LSIの配線構造は、垂直方向および水平方向の配線格子が定義された第1の配線層1および第2の配線層2と、第1の配線層1および第2の配線層2に定義された垂直方向および水平方向の配線格子の各格子点の対角を結ぶ斜めの配線格子が定義された第3の配線層3とから構成されている。

次に、このように構成された本実施例のマスクスライス方式LSIの配線構造における配線経路について、第2図～第4図を参照しながら具体的に説明する。

第2図に示すように、垂直方向格子間隔および水平方向格子間隔をともにdとしたときに配線ネットの端子11および端子12間の配線長が高速動作を必要とするLSIの遅延時間等の制約を満足するために8d以内であるという制限がある場

合を例にとりて説明すると、端子11および端子12間を結ぶ直線の角度が0度または90度に近いものから順に第1の配線層1および第2の配線層2を用いて配線する配線処理を行った結果、第3図に示すように、配線経路101と配線経路102とによって端子11および端子12間の配線が迂回せられ、配線長12dの配線経路201が得られたときに、第4図に示すように、配線経路101および102を修正せずに、端子11および端子12の位置に第1の配線層1および第3の配線層3間のスルーホール231および232を穿設し、端子11および端子12間を第3の配線層3を用いて斜めの配線を行うことにより、制限を満たす配線長

$$\begin{aligned} L &= \sqrt{(4d)^2 + (4d)^2} \\ &= 4\sqrt{2}d \end{aligned}$$

の配線経路221を得ることができる。

(発明の効果)

以上説明したように本発明は、高速動作を必要とするLSIの遅延時間等の制約を満足するため

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に設定された配線長の制限に対して第1の配線層および第2の配線層を用いて配線処理を行った後に制限を満たしていない配線を制限を満たすようにするために第3層の配線層を利用することにより、他の配線を移動したりブロックの配線位置を変更したりすることなしに、比較的容易に配線長の調整を行うことができる効果がある。

4. 図面の簡単な説明

第1図は本発明の一実施例に係るマスクスライス方式LSIの配線構造を示す図、

第2図は配線ネットの端子ペアの一例を示す図、

第3図は第1の配線層および第2の配線層を用いた配線処理後の配線例を示す図、

第4図は第3の配線層を用いて入手修正を行った後の配線例を示す図、

第5図は第1の配線層および第2の配線層を用いて入手修正を行った後の配線例を示す図である。

図において、

1・・・第1の配線層、

2・・・第2の配線層、

3・・・第3の配線層、

101、102、221・・・配線経路、

231、232・・・スルーホール、

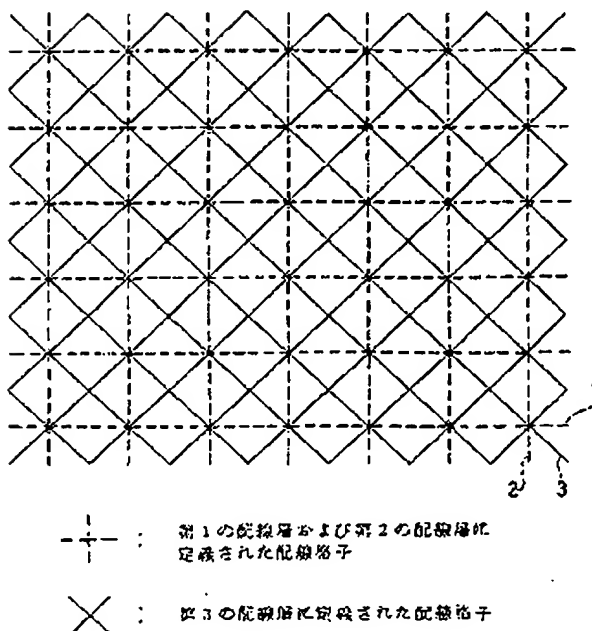
11、12・・・端子である。

特許出願人 日 本 電 気 株 式 会 社

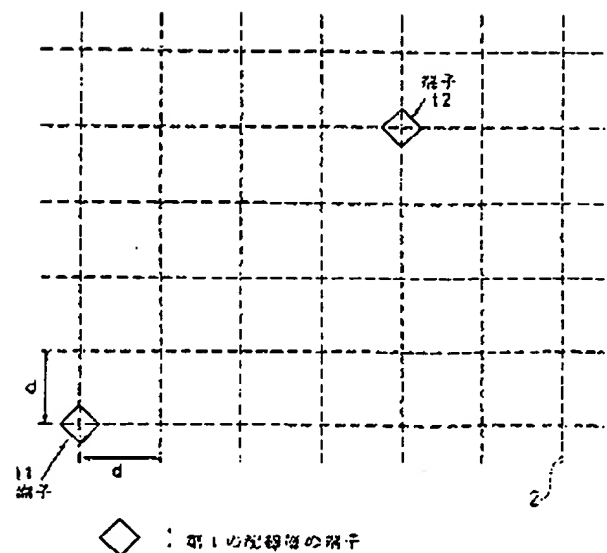
北陸日本電気ソフトウェア株式会社

代 理 人 弁 理 士 河 崎 純 一

第 1 図

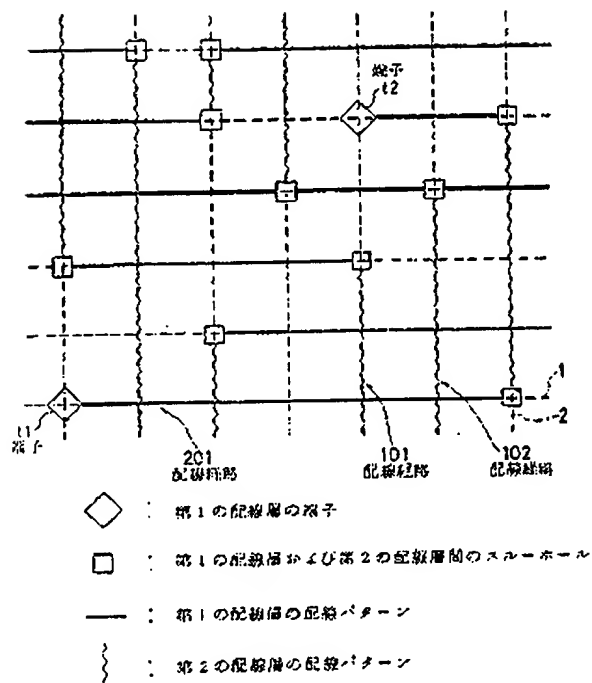


第 2 図

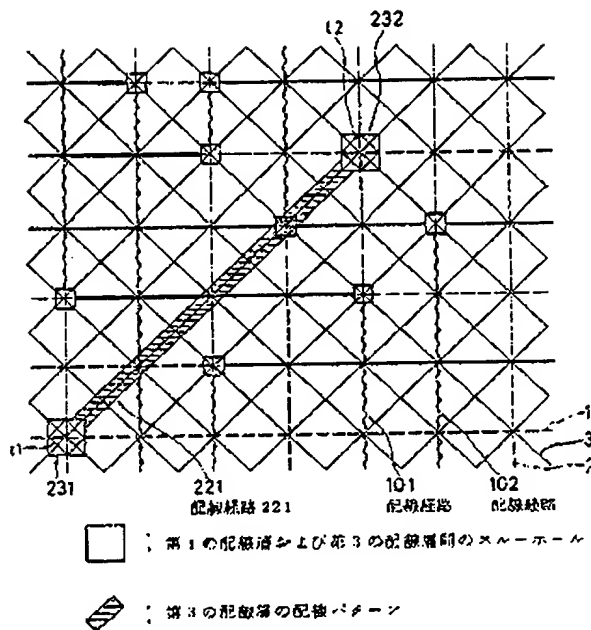


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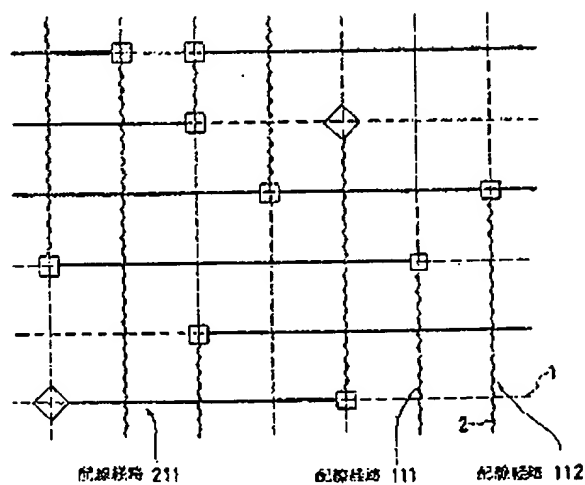
第 3 図



第 4 図



第 5 図



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SOFTWARE KK

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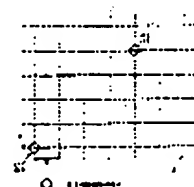
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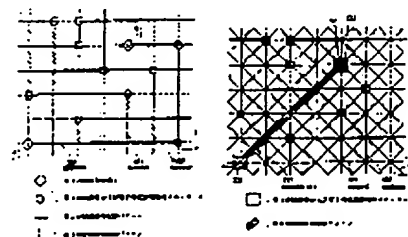
(54) WIRING STRUCTURE OF MASTER SLICE SYSTEM LSI

(57)Abstract:

PURPOSE: To comparatively easily adjust wiring length by arranging a first and a second wiring layer wherein a vertical and a horizontal wiring lattice are defined and a third wiring layer wherein a wiring lattice connecting diagonal lines of both lattices is defined.



CONSTITUTION: When both of the lattice intervals in the vertical and the horizontal directions are (d), the wiring length between the terminals t1 and t2 of a wiring network is shorter than or equal to 8d, in order to satisfy restrictions like the delay time of an LSI required for high speed operation. When wiring process is performed by using a first and a second wiring layer 2 in accordance with the order that the angle of the line connecting the terminals t1 and t2 is approximate to 0° or 90°, the wiring between the terminal t1 and t2 is detoured by wiring routes 101 and 102, and a wiring route 201 of α length 12d is obtained. On the other hand, by constituting an oblique wiring between the terminals t1 and t2 by using the layer 3, a wiring route 221 of a length $l=4.22/d$ can be obtained as follows, the wiring routes 101 and 102 are not corrected, and through holes 231 and 232 between the first and the this wiring 1, 3 are arranged at the positions of the terminals t1 and t2.



LEGAL STATUS

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[Patent number]

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(54) Title of Invention

Master Slice LSI Wiring Structure

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Specification

1. Title of Invention

Master Slice LSI Wiring Structure

2. Claims

A master slice LSI wiring structure comprising:

a first wiring layer and a second wiring layer for which vertical-direction and horizontal-direction wiring lattice members are defined; and

a third wiring layer for which diagonal wiring lattice members are defined which join diagonals of vertical-direction and horizontal-direction lattice points defined in said first wiring layer and second wiring layer.

3. Detailed Description of Invention

[Field of the Invention]

This invention concerns a master slice LSI wiring structure, and more particularly concerns a master slice LSI wiring structure for producing LSIs, wherewith, using common masks prior to the wiring step, only masks pertaining to the wiring are designed and fabricated individually for each product type.

[Prior Art]

Conventionally, in this type of master slice LSI wiring structure, all of the wiring lattice members in the wiring layers are defined in the vertical direction and horizontal direction (cf. "Ronri Sochi no CAD [Logic Device CADs]", Joho Shori Gakkai (Japan Society for Information Processing), March 20, 1981).

A case is now described wherein, as diagrammed in Fig. 2, when both the vertical direction lattice member interval and the horizontal direction lattice member interval are made d , and the wiring length between the terminals $t1$ and $t2$ in the wiring network is limited to $8d$ or less in order to satisfy restrictions such as the LSI delay time required for high-speed operation, as a result of implementing a wiring process that does the wiring using the first wiring layer 1 and the second wiring layer 2 sequentially from an angle of the straight line connecting the terminals $t1$ and $t2$ that is near either 0 or 90 degrees, the wiring between the terminals $t1$ and $t2$ is made circuitous by wiring paths 101 and 102, as diagrammed in Fig. 3, yielding the wiring path 201 having a wiring length of $12d$, whereupon, with the conventional master slice LSI wiring structure, as diagrammed in Fig. 5, the wiring paths 101 and 102 are altered manually to yield wiring paths 111 and 112, whereby the wiring path 211 having a wiring length of $8d$ which

satisfies the restriction is obtained.

[Problems Which the Present Invention Attempts to Solve]

With the conventional master slice LSI wiring structure described in the foregoing, if, after the wiring process in wiring a wiring net wherein a limitation is placed on the wiring length in order to satisfy a restriction such as the LSI delay time required for high-speed operation, that limitation has not been met, it is necessary to alter the wiring, moving other wiring, in order to satisfy the limitation. Many steps are required for such alteration, which constitutes a shortcoming.

Furthermore, in cases where the wiring length limitation cannot be met even after the wiring has been altered, it is necessary to redo the wiring process, performing block placement alterations, etc., resulting in a further increase in processing time, which is a shortcoming.

In view of these shortcomings, an object of the present invention is to provide a master slice LSI wiring structure wherewith, using a third wiring layer for which diagonal wiring lattice members are defined which join diagonals of vertical-direction and horizontal-direction lattice points defined by the first wiring layer and the second wiring layer, wiring lengths can be adjusted with comparative ease, without moving the other wiring or changing block placement positions.

[Means Used to Solve the Abovementioned Problems]

The master slice LSI wiring structure of the present invention comprises: a first wiring layer and a second wiring layer for which vertical-direction and horizontal-direction wiring lattice members are defined; and a third wiring layer for which diagonal wiring lattice members are defined which join diagonals of vertical-direction and horizontal-direction lattice points defined in the first wiring layer and second wiring layer.

[Operation]

In the master slice LSI wiring structure of the present invention, vertical direction and horizontal direction wiring lattice members are defined in the first wiring layer and the second wiring layer, and diagonal wiring lattice members are defined in the third wiring layer, which diagonal wiring lattice members join the diagonals of the lattice points of the horizontal direction and vertical direction wiring lattice members defined in the first wiring layer and the second wiring layer.

[Embodiments]

The present invention is now described in detail, making reference to the drawings.

Fig. 1 is a diagram of a master slice LSI wiring structure in one embodiment of the present invention. The master slice LSI wiring structure in this embodiment comprises: a first wiring layer and a second wiring layer 2 for which vertical-direction and horizontal-direction

wiring lattice members are defined; and a third wiring layer 3 for which diagonal wiring lattice members are defined which join diagonals of vertical-direction and horizontal-direction lattice points defined in the first wiring layer 1 and second wiring layer 2.

The process of implementing the wiring in the master slice LSI wiring structure in this embodiment, configured as stated, is now described specifically, with reference to Fig. 2 to 4.

The case is [again] described wherein, as diagrammed in Fig. 2, when both the vertical direction lattice member interval and the horizontal direction lattice member interval are made d , and the wiring length between the terminals $t1$ and $t2$ in the wiring network is limited to $8d$ or less in order to satisfy restrictions such as the LSI delay time required for high-speed operation, as a result of implementing a wiring process that does the wiring using the first wiring layer 1 and the second wiring layer 2 sequentially from an angle of the straight line connecting the terminals $t1$ and $t2$ that is near either 0 or 90 degrees, the wiring between the terminals $t1$ and $t2$ is made circuitous by wiring paths 101 and 102, as diagrammed in Fig. 3, yielding the wiring path 201 having a wiring length of $12d$, whereupon, as diagrammed in Fig. 4, without altering the wiring paths 101 and 102, through holes 231 and 232 are opened between the first wiring layer 1 and the third wiring layer 3 at the positions of the terminals $t1$ and $t2$, [respectively,] and diagonal wiring is implemented between terminal $t1$ and terminal $t2$ using the third wiring layer 3, thereby obtaining a wiring path 221 having a wiring length equal to

$$L = \sqrt{(4d)^2 + (4d)^2}$$

$$= 4\sqrt{2}d$$

which meets the limitation.

[Benefits of Invention]

After wiring processing has been performed using a first wiring layer and a second wiring layer, and there exists wiring that does not meet a wiring length limitation established to satisfy a restriction such as an LSI delay time required for high-speed operation, the present invention, as described in the foregoing, employs a third wiring layer to make that wiring meet that limitation, thereby making it possible to adjust wiring lengths with comparative ease without moving the other wiring or altering block placement positions.

4. Brief Description of Drawings

Fig. 1 is a diagram of a master slice LSI wiring structure in one embodiment of the present invention;

Fig. 2 is a diagram of one example of a pair of terminals in a wiring network;

Fig. 3 is a diagram of an example of wiring after the implementation of a wiring process using a first wiring layer and a second wiring layer;

Fig. 4 is a diagram of an example of wiring after a manual alteration using a third wiring

layer; and

Fig. 5 is a diagram of an example of wiring after performing a manual alteration using a first wiring layer and a second wiring layer.

The following reference characters are used in the drawings.

- 1 First wiring layer
- 2 Second wiring layer
- 3 Third wiring layer
- 101, 102, 221 Wiring paths
- 231, 232 Through holes
- t1, t2 Terminals

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	Hokuriku NEC Software, Ltd.
Agent	Junichi Kawahara, patent attorney

Figure 1

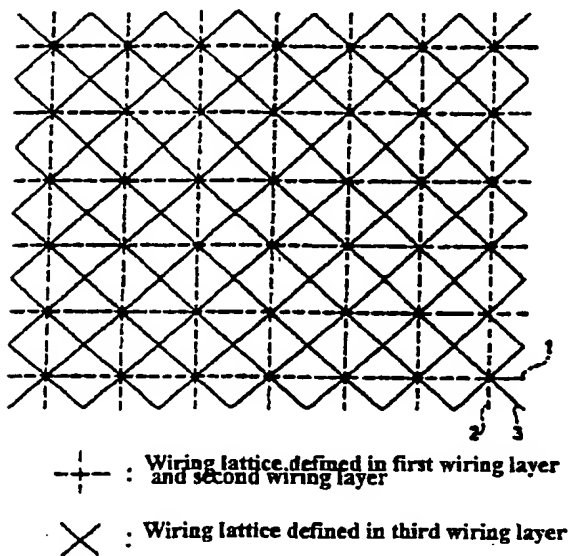


Figure 2

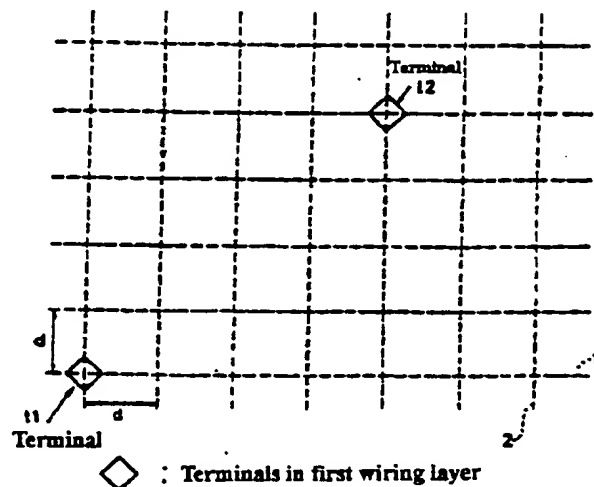


Figure 3

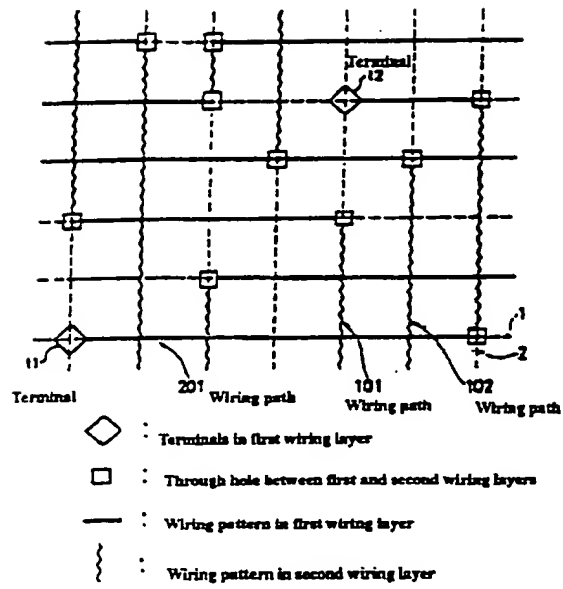


Figure 4

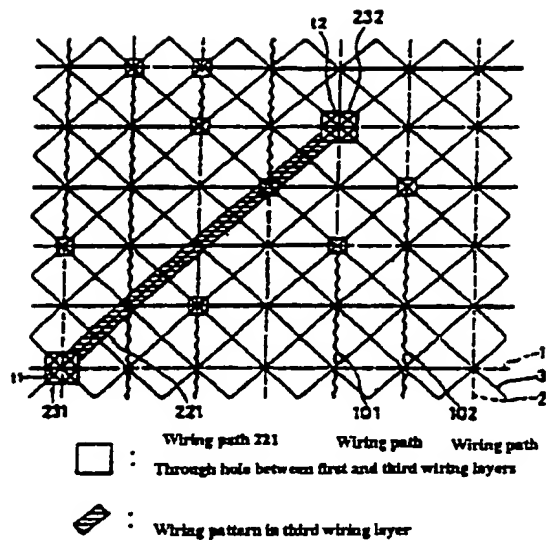
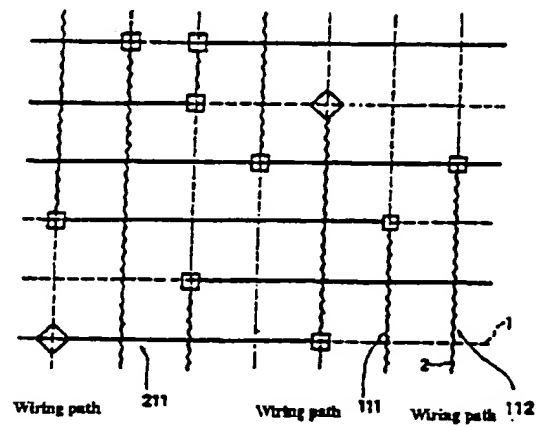


Figure 5



[Translator's Notes]

1. The original term koushi, usually translated "lattice" (and sometimes "grating" or "grid") is herein translated "lattice member" because the English word "lattice" refers to the entire lattice and never to its constituent elements or "members" as is apparently intended here.
2. The term haisen, as used in microchip technology, may also be translated "interconnect," but is translated by the more common "wiring" herein to avoid confusion.
3. The original language [A] ni teigi sareta [B], which occurs frequently in the text, is ambiguous. I have translated it "B defined in A," but it could also mean "B defined by A."

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